





Features:

- RoHS Compliant
- 100 Watts
- DC 3.5 GHz
- AIN Ceramic
- Non-Nichrome Resitive Element
- Low VSWR
- 100% Tested
- Small Size

Description:

The A100N50X4A is high performance Aluminum Nitride (AIN) chip termination intended as an alternative to Beryllium Oxide (BeO). The termination is well suited to all cellular frequency bands such as; AMPS, GSM, DCS, PCS, PHS and UMTS. The high power handling makes the part ideal for terminating circulators and for use in power combiners. The termination is also RoHS compliant!

General Specifications:

Resistive Element	Thick film
Substrate	AIN Ceramic
Terminal Finish	Matte Tin over Nickel Barrier
Operating Temperature	-55 to +150°C (see de rating chart)

Tolerance is ± 0.010 ", unless otherwise specified. Designed to meet or exceed applicable portions of MIL-E-5400. All dimensions in inches.

Electrical Specifications:

 Resistive Value:
 50 Ohms, ± 2%

 Power:
 100 Watts

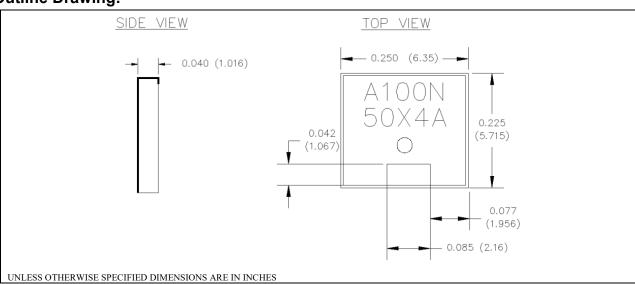
 Frequency Range:
 DC – 3.5 GHz

 V.S.W.R:
 1.12 : 1 DC – 3.0 GHz

 1.22 : 1 DC – 3.5 GHz

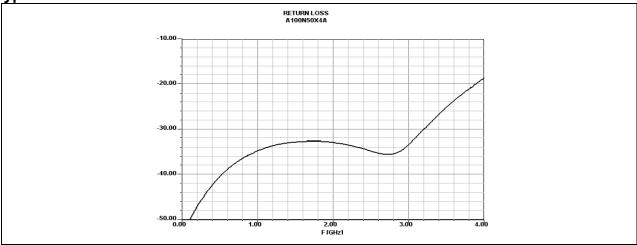
Specification based on unit properly installed using suggested mounting instructions and a 50 ohm nominal impedance. Specifications subject to change.

Outline Drawing:

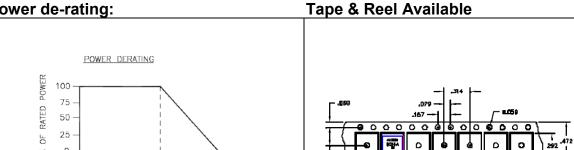




Typical Performance:

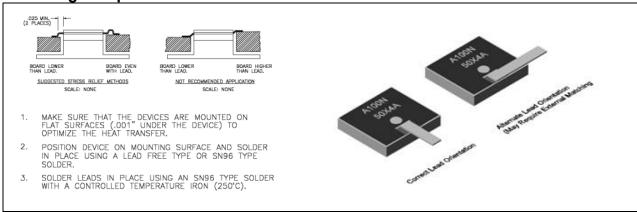


Power de-rating:



Mounting Footprint and Procedure:

75 SOLDER INTERFACE TEMPERATURE - 'C



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